



# 3DD102

## NPN Silicon Low Frequency High Power Transistor



**Features:**

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP

**TECHNICAL DATA:**

(Ta = 25°C )

Parameter name	Symbols	Unit	Specifications					Test Condition
			A	B	C	D	E	
Collector-Emitter Voltage	V <sub>CEO</sub>	V	100	150	200	250	300	
Emitter-Base Voltage	V <sub>EBO</sub>	V	4					
Max. Collector Current	I <sub>CM</sub>	A	5					
Max. Collector Dissipation	P <sub>CM</sub>	W	50					T <sub>c</sub> :75°C
Junction Temperature	T <sub>jm</sub>	°C	175					
Storage Temperature	T <sub>stg</sub>	°C	-55~+175					
Collector-Emitter Leakage Current	I <sub>CEO</sub>	mA	Max.:1.0					V <sub>CE</sub> =50V
Collector- Emitter Saturation Voltage Drop	V <sub>CE(sat)</sub>	V	Max.:0.8			Max.:1.5		I <sub>c</sub> =2.5A,I <sub>B</sub> =0.25A
DC Current Gain	h <sub>FE</sub>		Min.:20,Max.:120					V <sub>CE</sub> =5V,I <sub>c</sub> =2A
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	V	A	B	C	D	E	I <sub>c</sub> =1mA
			100	150	200	250	300	
E-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	V	4					I <sub>E</sub> =1mA

**hFE Colored:**

Color	Brown	Red	Orange
h <sub>FE</sub>	20~40	40~80	80~120

**Outline and Dimensions:**